

1.2V Drive Nch MOSFET

RUE002N05

Structure

Silicon N-channel MOSFET

Features

- 1) High speed switing.
- 2) Small package(EMT3).
- 3)Ultra low voltage drive(1.2V drive).

Application

Switching

Packaging specifications

Туре	Package	Taping	
	Code	TL	
	Basic ordering unit (pieces)	3000	
RUE002N0	0		

● Absolute maximum ratings (Ta = 25°C)

Param	Symbol	Limits	Unit	
Drain-source voltage		V_{DSS}	50	V
Gate-source voltage		V_{GSS}	±8	V
Drain current	Continuous	I _D	±200	mA
	Pulsed	I _{DP} *1	±800	mA
Source current	Continuous	I _S	125	mA
(Body Diode)	Pulsed	I _{SP} *1	800	mA
Power dissipation		P _D *2	150	mW
Channel temperature		Tch	Tch 150	
Range of storage temperature		Tstg -55 to +150		°C

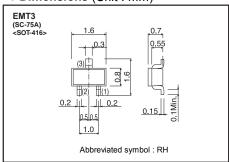
^{*1} Pw≤10μs, Duty cycle≤1%

• Thermal resistance

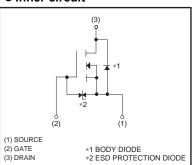
Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	833	°C / W

^{*} Each terminal mounted on a recommended land.

• Dimensions (Unit : mm)



• Inner circuit



^{*2} Each terminal mounted on a recommended land.

RUE002N05 Data Sheet

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	1	-	±10	μA	$V_{GS}=\pm 8V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	50	-	1	٧	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	1	-	1	μA	V_{DS} =50V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.3	-	1.0	٧	V _{DS} =10V, I _D =1mA
		1	1.6	2.2		I _D =200mA, V _{GS} =4.5V
Static ducin course on state		1	1.7	2.4	Ω	I _D =200mA, V _{GS} =2.5V
Static drain-source on-state resistance	R _{DS (on)} *	1	1.9	2.7		I _D =100mA, V _{GS} =1.8V
resistantes		1	2.0	4.0		I _D =40mA, V _{GS} =1.5V
		1	2.4	7.2		I _D =20mA, V _{GS} =1.2V
Forward transfer admittance	I Y _{fs} I*	0.4	-	-	S	I _D =200mA, V _{DS} =10V
Input capacitance	C _{iss}	1	25	-	pF	V _{DS} =10V
Output capacitance	C _{oss}	1	6	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	1	3	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	1	4	-	ns	I _D =100mA, V _D 5 30V
Rise time	t _r *	1	6	-	ns	V _{GS} =4.5V
Turn-off delay time	t _{d(off)} *		15	-	ns	R_L =300 Ω
Fall time	t _f *	-	55	-	ns	R_G =10 Ω

^{*}Pulsed

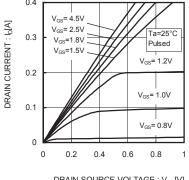
●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V _{SD} *	-	-	1.2	V	I _s =200mA, V _{GS} =0V

^{*}Pulsed

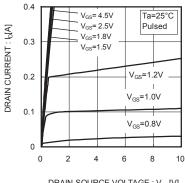
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Electrical characteristic curves



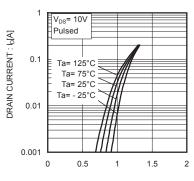
DRAIN-SOURCE VOLTAGE : VDS[V]

Fig.1 Typical Output Characteristics(I)



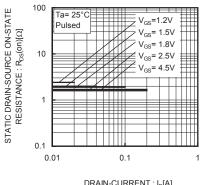
DRAIN-SOURCE VOLTAGE: VDS[V]

Fig.2 Typical Output Characteristics(II)



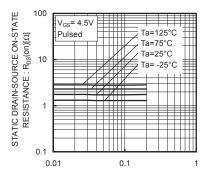
GATE-SOURCE VOLTAGE: VGS[V]

Fig.3 Typical Transfer Characteristics



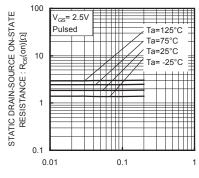
DRAIN-CURRENT : $I_D[A]$

Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)



DRAIN-CURRENT : I_D[A]

Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)



DRAIN-CURRENT : In[A]

Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

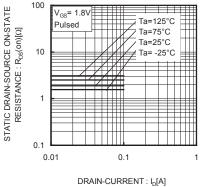


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

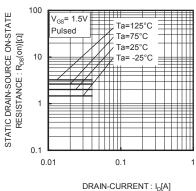
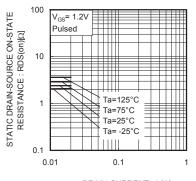


Fig.8 Static Drain-Source On-State

Resistance vs. Drain Current(V)



DRAIN-CURRENT : I_D[A]

Fig.9 Static Drain-Source On-State Resistance vs. Drain Current(VI) **RUE002N05 Data Sheet**

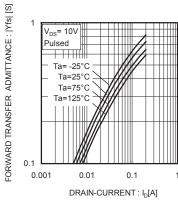


Fig.10 Forward Transfer Admittance vs. Drain Current

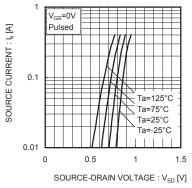


Fig.11 Reverse Drain Current vs. Sourse-Drain Voltage

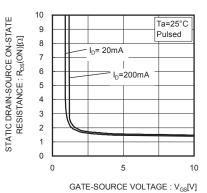


Fig.12 Static Drain-Source On-State Resistance vs. Gate Source Voltage

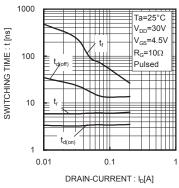
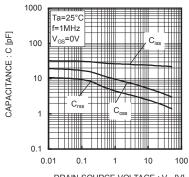


Fig.13 Switching Characteristics



DRAIN-SOURCE VOLTAGE : $V_{DS}[V]$ Fig.14 Typical Capacitance vs. Drain-Source Voltage

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●Measurement circuits

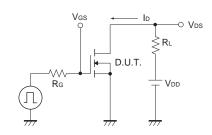


Fig.1-1 Switching time measurement circuit

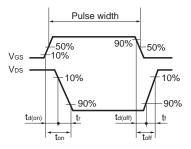


Fig.1-2 Switching waveforms

●Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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